# Volkmar Dierolf

List of Publications by Year
in descending order

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|---|---|---|---|
| 124 papers | 3,010 citations | 185998 28 h-index | 174990 52 g-index |

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|---|---|---|---|
| 128 all docs | 128 docs citations | 128 times ranked | 2260 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Approaches for high internal quantum efficiency green InGaN light-emitting diodes with large overlap quantum wells. Optics Express, 2011, 19, A991. | 1.7 | 535 |
| 2 | Defectâ€“Domain Wall Interactions in Trigonal Ferroelectrics. Annual Review of Materials Research, 2007, 37, 449-489. | 4.3 | 229 |
| 3 | Growths of staggered InGaN quantum wells light-emitting diodes emitting at 520â€“525 nm employing graded growth-temperature profile. Applied Physics Letters, 2009, 95, . | 1.5 | 150 |
| 4 | Stability of intrinsic defects and defect clusters in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">Li</mml:mi><mml:mi mathvariant="normal">Nb</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>from density functional theory calculations. Physical Review B, 2008, 78, . | 1.1 | 109 |
| 5 | Perspective: Toward efficient GaN-based red light emitting diodes using europium doping. Journal of Applied Physics, 2018, 123, . | 1.1 | 100 |
| 6 | Design and characteristics of staggered InGaN quantum-well light-emitting diodes in the green spectral regime. IET Optoelectronics, 2009, 3, 283-295. | 1.8 | 91 |
| 7 | Enhanced room-temperature luminescence efficiency through carrier localization in AlxGa1â^'xN alloys. Applied Physics Letters, 2005, 86, 031916. | 1.5 | 90 |
| 8 | Direct laser-writing of ferroelectric single-crystal waveguide architectures in glass for 3D integrated optics. Scientific Reports, 2015, 5, 10391. | 1.6 | 83 |
| 9 | Directionally controlled 3D ferroelectric single crystal growth in LaBGeO_5 glass by femtosecond laser irradiation. Optics Express, 2009, 17, 23284. | 1.7 | 72 |
| 10 | Combined excitation-emission spectroscopy ofEr3+ions in stoichiometricLiNbO3:The site selectivity of direct and up conversion excitation processes. Physical Review B, 2000, 61, 8043-8052. | 1.1 | 68 |
| 11 | Direct-write method for domain inversion patterns in LiNbO3. Applied Physics Letters, 2004, 84, 3987-3989. | 1.5 | 58 |
| 12 | Excitation pathways and efficiency ofÂEuÂions inÂGaN byÂsite-selective spectroscopy. Applied Physics B: Lasers and Optics, 2009, 97, 607-618. | 1.1 | 56 |
| 13 | The influence of 180Â° ferroelectric domain wall width on the threshold field for wall motion. Journal of Applied Physics, 2008, 104, 084107. | 1.1 | 53 |
| 14 | Site-selective spectroscopy of Er in GaN. Journal of Applied Physics, 2004, 95, 5464-5470. | 1.1 | 52 |
| 15 | Site and sample dependent electronâ€“phonon coupling of Eu ions in epitaxial-grown GaN layers. Optical Materials, 2011, 33, 1050-1054. | 1.7 | 48 |
| 16 | Structure and energetics of ferroelectric domain walls in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>LiNbO</mml:mtext></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:r atomic-level simulations. Physical Review B, 2010, 82, . | 1.1 | 45 |
| 17 | The role of donor-acceptor pairs in the excitation of Eu-ions in GaN:Eu epitaxial layers. Journal of Applied Physics, 2014, 115, . | 1.1 | 45 |
| 18 | Ferroelectric domain imaging by defect-luminescence microscopy. Journal of Applied Physics, 2003, 93, 2295-2297. | 1.1 | 44 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Excitation of Eu3+ in gallium nitride epitaxial layers: Majority versus trap defect center. Applied Physics Letters, 2011, 98, 011102. | 1.5 | 44 |
| 20 | Present understanding of Eu luminescent centers in Eu-doped GaN grown by organometallic vapor phase epitaxy. Japanese Journal of Applied Physics, 2014, 53, 05FA13. | 0.8 | 42 |
| 21 | Inspection of periodically poled waveguide devices by confocal luminescence microscopy. Applied Physics B: Lasers and Optics, 2004, 78, 363-366. | 1.1 | 41 |
| 22 | Stability and charge transfer levels of extrinsic defects in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>LiNbO</mml:mtext></mml:mrow><mml:mn>3</mml:mn></mml:r Physical Review B, 2010, 82, . | 1.1 | 41 |
| 23 | Structure and energetics of Er defects in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>LiNbO</mml:mtext></mml:mrow><mml:mn>3</mml:mn></mml:r first-principles and thermodynamic calculations. Physical Review B, 2009, 80, . | 1.1 | 35 |
| 24 | Luminescence properties of Eu-doped GaN under resonant excitation and quantitative evaluation of luminescent sites. Journal of Applied Physics, 2013, 114, . | 1.1 | 35 |
| 25 | Raman studies of ferroelectric domain walls in lithium tantalate and niobate. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 830-833. | 0.8 | 33 |
| 26 | Combined excitation emission spectroscopy of defects for site-selective probing of ferroelectric domain inversion in lithium niobate. Journal of Luminescence, 2007, 125, 67-79. | 1.5 | 31 |
| 27 | Demonstration of single crystal growth via solid-solid transformation of a glass. Scientific Reports, 2016, 6, 23324. | 1.6 | 30 |
| 28 | Fabrication of graded index single crystal in glass. Scientific Reports, 2017, 7, 44327. | 1.6 | 30 |
| 29 | Femtosecond laser-writing of 3D crystal architecture in glass: Growth dynamics and morphological control. Materials and Design, 2018, 146, 228-238. | 3.3 | 30 |
| 30 | Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. Scientific Reports, 2016, 6, 18808. | 1.6 | 29 |
| 31 | Laser fabrication of semiconducting ferroelectric single crystal SbSI features on chalcohalide glass. Optical Materials Express, 2011, 1, 652. | 1.6 | 27 |
| 32 | Frequency shift of Raman modes due to an applied electric field and domain inversion in LiNbO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review B, 2011, 84, . | 1.1 | 26 |
| 33 | Influence of ferroelectric domain walls on the Raman scattering process in lithium tantalate and niobate. Optics Letters, 2012, 37, 1032. | 1.7 | 26 |
| 34 | Crystal-field split levels of Nd3+ ions in GaN measured by luminescence spectroscopy. Journal of Applied Physics, 2009, 105, 053101. | 1.1 | 23 |
| 35 | Rotating lattice single crystal architecture on the surface of glass. Scientific Reports, 2016, 6, 36449. | 1.6 | 22 |
| 36 | Charge state of vacancy defects in Eu-doped GaN. Physical Review B, 2017, 96, . | 1.1 | 20 |

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|---|---|---|---|
| 37 | High-resolution site selective optical spectroscopy of rare earth and transition metal defects in insulators. Journal of Luminescence, 2000, 87-89, 989-991. | 1.5 | 19 |
| 38 | Shape of ferroelectric domains in LiNbO3 and LiTaO3 from defect/domain-wall interactions. Applied Physics Letters, 2011, 98, . | 1.5 | 19 |
| 39 | Site-selective spectroscopy of Er3+:Ti:LiNbO3 waveguides. Applied Physics B: Lasers and Optics, 2001, 72, 803-810. | 1.1 | 17 |
| 40 | Luminescence Properties of Eu-Doped GaN Grown on GaN Substrate. Japanese Journal of Applied Physics, 2013, 52, 08JM03. | 0.8 | 17 |
| 41 | Confocal two photon emission microscopy: A new approach to waveguide imaging. Journal of Luminescence, 2003, 102-103, 201-205. | 1.5 | 16 |
| 42 | Local probing of the interaction between intrinsic defects and ferroelectric domain walls in lithium niobate. Applied Physics Letters, 2013, 102, . | 1.5 | 16 |
| 43 | Effect of thermal annealing on luminescence properties of Eu,Mg-codoped GaN grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2013, 102, 141904. | 1.5 | 16 |
| 44 | Thermodynamics and Kinetics of Three<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Mg</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi mathvariant="normal">H</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mml:mrow><mml:mi>V</mml:mi></mml:mrow><mml:mrow><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math>Complexes in Mg:GaN from Combined First-Principles Calculation and Experiment. Physical Review Letters, 2014, 112, . | 7.9 | 16 |
| 45 | Crystallization of Stoichiometric <scp>SbSI</scp> Glass. Journal of the American Ceramic Society, 2014, 97, 198-205. | 1.9 | 16 |
| 46 | Electron-beam-induced migration of hydrogen in Mg-doped GaN using Eu as a probe. Physical Review B, 2013, 88, . | 1.1 | 15 |
| 47 | Color-Tunablility in GaN LEDs Based on Atomic Emission Manipulation under Current Injection. ACS Photonics, 2019, 6, 1153-1161. | 3.2 | 15 |
| 48 | The role of defects in light induced domain inversion in lithium niobate. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 136-140. | 0.8 | 14 |
| 49 | Challenges of CW laser-induced crystallization in a chalcogenide glass. Optical Materials Express, 2013, 3, 1026. | 1.6 | 14 |
| 50 | Laser Fabrication of Two-Dimensional Rotating-Lattice Single Crystal. Crystal Growth and Design, 2017, 17, 1735-1746. | 1.4 | 14 |
| 51 | Pathway Towards High-Efficiency Eu-doped GaN Light-Emitting Diodes. Scientific Reports, 2017, 7, 14648. | 1.6 | 14 |
| 52 | Influence of heat and UV light on the coercive field ofÂlithiumÂniobate crystals. Applied Physics B: Lasers and Optics, 2010, 101, 535-539. | 1.1 | 13 |
| 53 | Enhanced magnetization in erbium doped GaN thin films due to strain induced electric fields. Applied Physics Letters, 2011, 99, 122506. | 1.5 | 12 |
| 54 | Vibrationally induced center reconfiguration in co-doped GaN:Eu, Mg epitaxial layers: Local hydrogen migration vs. activation of non-radiative channels. Applied Physics Letters, 2013, 103, . | 1.5 | 12 |

| # | Article | IF | Citations |
|---|---|---|---|
| 55 | Optical properties and structure of Er:LaBGeO_5 laser-induced crystals-in-glass. Optical Materials Express, 2017, 7, 4095. | 1.6 | 12 |
| 56 | Molecular dynamics simulation of the effect of cooling rate on the structure and properties of lithium disilicate glass. Journal of Non-Crystalline Solids, 2021, 569, 120991. | 1.5 | 11 |
| 57 | Near-infrared photoluminescence properties of neodymium in in situ doped AlN grown using plasma-assisted molecular beam epitaxy. Optical Materials Express, 2011, 1, 78. | 1.6 | 10 |
| 58 | Re-Excitation of Trivalent Europium Ions Doped into Gallium Nitride Revealed through Photoluminescence under Pulsed Laser Excitation. ACS Photonics, 2018, 5, 875-880. | 3.2 | 10 |
| 59 | Challenges of Laser-Induced Single-Crystal Growth in Glass: Incongruent Matrix Composition and Laser Scanning Rate. Crystal Growth and Design, 2019, 19, 4489-4497. | 1.4 | 10 |
| 60 | Evolution of glass structure during femtosecond laser assisted crystallization of LaBGeO5 in glass. Journal of Non-Crystalline Solids, 2021, 551, 120396. | 1.5 | 10 |
| 61 | Spectral line broadening mechanism of Er3+ transitions in Er:Ti:LiNbO3 channel waveguides. Applied Physics B: Lasers and Optics, 2001, 73, 443-448. | 1.1 | 9 |
| 62 | Crystal-field analysis and Zeeman splittings of energy levels of Nd3+ (4f3) in GaN. Journal of Applied Physics, 2011, 110, . | 1.1 | 9 |
| 63 | Defect roles in the excitation of Eu ions in Eu:GaN. Optics Express, 2013, 21, 30633. | 1.7 | 9 |
| 64 | Formation of Ferroelectric Phases in Sbâ€“Sâ€“I Glasses. Journal of the American Ceramic Society, 2014, 97, 3458-3462. | 1.9 | 9 |
| 65 | Ferroelectric domain engineering of lithium niobate single crystal confined in glass. MRS Communications, 2019, 9, 334-339. | 0.8 | 9 |
| 66 | Laser-induced growth of oriented Sb2S3 single crystal dots on the surface of 82SbSIâ€“18Sb2S3 glasses. Journal of Non-Crystalline Solids, 2016, 431, 36-40. | 1.5 | 8 |
| 67 | Comparative Studies of Er3â˜Ž Ions in LiNbO3Waveguides Produced by Different Methods. Radiation Effects and Defects in Solids, 2003, 158, 263-267. | 0.4 | 7 |
| 68 | Site-specific excitation of Eu ions in GaN. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 30-33. | 0.8 | 7 |
| 69 | Formation of laser-induced SbSI single crystal architecture in Sbâ€“Sâ€“I glasses. Journal of Non-Crystalline Solids, 2013, 377, 245-249. | 1.5 | 7 |
| 70 | Physics of Efficiency Droop in GaN:Eu Light-Emitting Diodes. Scientific Reports, 2017, 7, 16773. | 1.6 | 7 |
| 71 | Rearrangement of Rare Earth Defects Under Domain Inversion in LiNbO3. Radiation Effects and Defects in Solids, 2003, 158, 247-250. | 0.4 | 6 |
| 72 | Combined Excitation Emission Spectroscopy of Europium ions in GaN and AlGaN Films. Materials Research Society Symposia Proceedings, 2005, 866, 84. | 0.1 | 6 |

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|---|---|---|---|
| 73 | Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. Journal of Applied Physics, 2020, 127, 013102. | 1.1 | 6 |
| 74 | Energy levels of Nd3+ ions in GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S671-S674. | 0.8 | 5 |
| 75 | The source of lattice rotation in rotating lattice single (RLS) crystals. Scripta Materialia, 2021, 193, 22-26. | 2.6 | 5 |
| 76 | Temporally modulated energy shuffling in highly interconnected nanosystems. Nanophotonics, 2020, 10, 851-876. | 2.9 | 5 |
| 77 | Determination of the structure of lithium niobosilicate glasses by molecular dynamics simulation with a new Nb-O potential. Computational Materials Science, 2022, 207, 111307. | 1.4 | 5 |
| 78 | Analytical form of frequency dependence of dgd in concatenated single-mode fiber systems. Journal of Lightwave Technology, 2003, 21, 2217-2223. | 2.7 | 4 |
| 79 | Identification of defect-trap-related europium sites in gallium nitride. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 834-837. | 0.8 | 4 |
| 80 | Nature and Excitation Mechanism of the Emission-dominating Minority Eu-center in GaN Grown by Organometallic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2011, 1342, 67. | 0.1 | 4 |
| 81 | Fabrication of single crystal architecture in Sb-S-I glass: Transition from dot to line. Journal of Non-Crystalline Solids, 2018, 501, 43-48. | 1.5 | 4 |
| 82 | Influence of the Laser Scanning Rate on the Structure of Rotating Lattice Single Crystal Lines. Crystal Growth and Design, 2019, 19, 6324-6330. | 1.4 | 4 |
| 83 | Effects of Surface Orientation and Termination Plane on Glassâ€toâ€Crystal Transformation of Lithium Disilicate by Molecular Dynamics Simulations. Physica Status Solidi (B): Basic Research, 2021, 258, 2000427. | 0.7 | 4 |
| 84 | Curved lattices of crystals formed in glass. International Journal of Applied Glass Science, 0, , . | 1.0 | 4 |
| 85 | Multistep Resonant Excitation of Erbium Ions in Thin Silicon Oxide Layers. Materials Research Society Symposia Proceedings, 2005, 866, 41. | 0.1 | 3 |
| 86 | Ferroelectric Materials. , 2006, , 6-1-6-66. | | 3 |
| 87 | Site Selective Magneto-Optical Studies of Eu ions in Gallium Nitride. Materials Research Society Symposia Proceedings, 2011, 1342, 93. | 0.1 | 3 |
| 88 | Growth of Eu-doped GaN and its magneto-optical properties. , 2016, , 259-280. | | 3 |
| 89 | Picosecond time-resolved dynamics of energy transfer between GaN and the various excited states of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">E</mml:mi><mml:msup><mml:mrow><mml:mi mathvariant="normal">u</mml:mi></mml:mrow><mml:mrow><mml:mn>3</mml:mn><mml:mo>+</mml:mo></mml:mrow></mml:msup></mml:mrow></mml:math> ions. Physical Review B, 2019, 100, . | 1.1 | 3 |
| 90 | Polarization and Surface Effects on the Seed Orientation of Laser-Induced Sb<sub>2</sub>S<sub>3</sub> Crystals on Sb-S-I Glass. Crystal Growth and Design, 2021, 21, 4276-4284. | 1.4 | 3 |

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|---|---|---|---|
| 91 | GaN Doped with Neodymium by Plasma-Assisted Molecular Beam Epitaxy for Potential Lasing Applications. Materials Research Society Symposia Proceedings, 2008, 1111, 1. | 0.1 | 2 |
| 92 | Effect of Laser Beam Profile on Rotating Lattice Single Crystal Growth in Sb2S3 Model Glass. Crystals, 2021, 11, 36. | 1.0 | 2 |
| 93 | Modeling defect mediated color-tunability in LEDs with Eu-doped GaN-based active layers. Journal of Applied Physics, 2022, 131, 045701. | 1.1 | 2 |
| 94 | The role of glass composition in the 3D laser fabrication of lithium niobate single crystal in lithium niobosilicate glass. Optical Materials, 2022, 128, 112380. | 1.7 | 2 |
| 95 | Confocal Photoluminescence and Cathodoluminescence Studies of AlGaN. Materials Research Society Symposia Proceedings, 2003, 798, 616. | 0.1 | 1 |
| 96 | Improved Photoluminescence of InGaN Quantum Wells Grown on Nano-Patterned AGOG Sapphire Substrate by Metalorganic Vapor Phase Epitaxy. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , . | 0.0 | 1 |
| 97 | Fluorescence in planar and ridge waveguides fabricated in Erbium-Doped lithium-niobate-on-insulator (Er:LNOI). , 2013, , . | | 1 |
| 98 | In situ study of rotating lattice singleâ€crystal formation in Sb 2 S 3 glass by Laue Î¼XRD. Journal of the American Ceramic Society, 2020, 103, 3954-3961. | 1.9 | 1 |
| 99 | Study of poled lithium niobate waveguide devices by confocal defect spectroscopy. , 0, , . | | 0 |
| 100 | In-situ confocal luminescence microscopy study of lithium niobate during domain inversion. , 0, , . | | 0 |
| 101 | Combined excitation emission spectroscopy of Eu-doped GaN. , 0, , . | | 0 |
| 102 | Real-time diagnostic of the defect-domain wall interaction in LiNbO/sub 3/ during domain inversion. , 2005, , . | | 0 |
| 103 | Site selective spectroscopy of Eu-doped GaN. , 2005, , . | | 0 |
| 104 | A Silicon-based Light Emitter. , 0, , . | | 0 |
| 105 | Luminescence and Raman Based Real Time Imaging of Ferroelectric Domain Walls. Materials Research Society Symposia Proceedings, 2006, 966, 1. | 0.1 | 0 |
| 106 | The Site Selectivity of the E-beam Excitation of Eu ion in GaN. , 2007, , . | | 0 |
| 107 | Physical and Optical Characterization of GaN Doped with Neodymium grown by Plasma-Assisted Molecular Beam Epixaty. , 2007, , . | | 0 |
| 108 | Near Field Optical Spectroscopy Studies of Carrier Localization in Al<inf>x</inf>Ga<inf>1-x</inf>N Alloys. , 2007, , . | | 0 |

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|---|---|---|---|
| 109 | Near Field Optical Imaging of Carrier Localization in Al<inf>x</inf>Ga<inf>1-x</inf>N Alloys. , 2007, , . | | 0 |
| 110 | Site-selective studies of erbium ion defects in thermally grown silicon oxides. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 749-752. | 0.8 | 0 |
| 111 | Defect based real-time diagnostics of ferroelectric domain wall motion. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 690-694. | 0.8 | 0 |
| 112 | Excitation Pathways of Rare Earth Ions by Energetic Electrons. Materials Research Society Symposia Proceedings, 2008, 1111, 1. | 0.1 | 0 |
| 113 | Spontaneous recombination rate and luminescence efficiency of staggered InGaN quantum wells light emitting diodes. , 2008, , . | | 0 |
| 114 | Characteristics of staggered InGaN quantum wells light-emitting diodes emitting at 480–525 nm. , 2009, , . | | 0 |
| 115 | Site Selective Spectroscopy on Erbium Ions in Stoichiometric Lithium Tantalate. Journal of Physics: Conference Series, 2010, 249, 012011. | 0.3 | 0 |
| 116 | Optical and magneto-optical properties of neodymium and erbium doped gallium nitride epilayers. , 2011, , . | | 0 |
| 117 | Domain walls in Lithium Niobate and Lithium Tantalate: Local structure and properties. , 2011, , . | | 0 |
| 118 | Probing Laser Induced Space Charge Fields with Rare Earth Dopants. Materials Research Society Symposia Proceedings, 2013, 1592, 1. | 0.1 | 0 |
| 119 | Nonlinear-optical response and Raman signals of nanocrystalline lithium niobate. , 2013, , . | | 0 |
| 120 | Light Aided Domain Patterning and Rare Earth Emission Based Imaging of Ferroelectric Domains. Springer Series in Materials Science, 2014, , 135-162. | 0.4 | 0 |
| 121 | Optical and magnetic characterization of III-N:Nd grown by molecular beam epitaxy. , 2016, , 281-312. | | 0 |
| 122 | Engineering the internal quantum efficiency of GaN:Eu based red light emitting diodes. , 2017, , . | | 0 |
| 123 | Single Crystal Growth via Solidâ€‰â†'â€‰Solid Transformation of Glass. Transactions of the Indian Institute of Metals, 2019, 72, 1971-1979. | 0.7 | 0 |
| 124 | Light Aided Domain Patterning and Rare Earth Emission Based Imaging of Ferroelectric Domains. Springer Series in Materials Science, 2009, , 137-164. | 0.4 | 0 |